

# **HAT2240C**

# Silicon N Channel MOS FET Power Switching

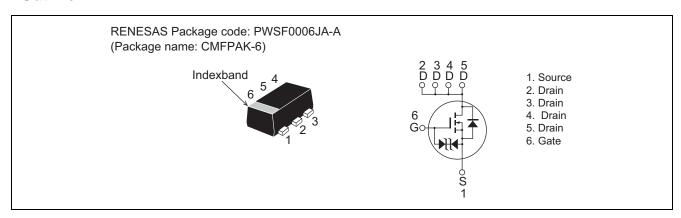
R07DS1184EJ0500 (Previous: REJ03G1241-0400)

> Rev.5.00 Mar 19, 2014

#### **Features**

- Low on-resistance  $R_{DS(on)} = 75 \text{ m}\Omega \text{ typ.} (\text{at } V_{GS} = 4.5 \text{ V})$
- Low drive current
- High density mounting
- 2.5 V gate drive device

#### **Outline**



## **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

			(14 =0 0)
Item	Symbol	Ratings	Unit
Drain to source voltage	V <sub>DSS</sub>	60	V
Gate to source voltage	V <sub>GSS</sub>	±12	V
Drain current	I <sub>D</sub>	2.5	А
Drain peak current	I <sub>D (pulse)</sub> Note1	10	А
Body - drain diode reverse drain current	I <sub>DR</sub>	2.5	А
Channel dissipation	Pch Note2	900	mW
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW  $\leq$  10  $\mu$ s, duty cycle  $\leq$  1%

2. When using the glass epoxy board (FR4 40 x 40 x 1.6mm)

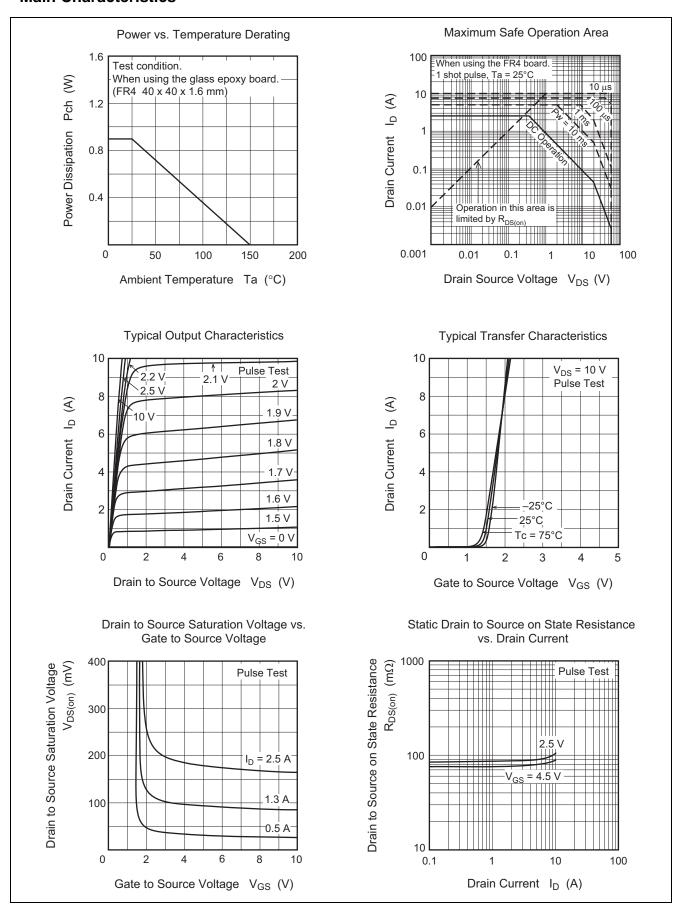
# **Electrical Characteristics**

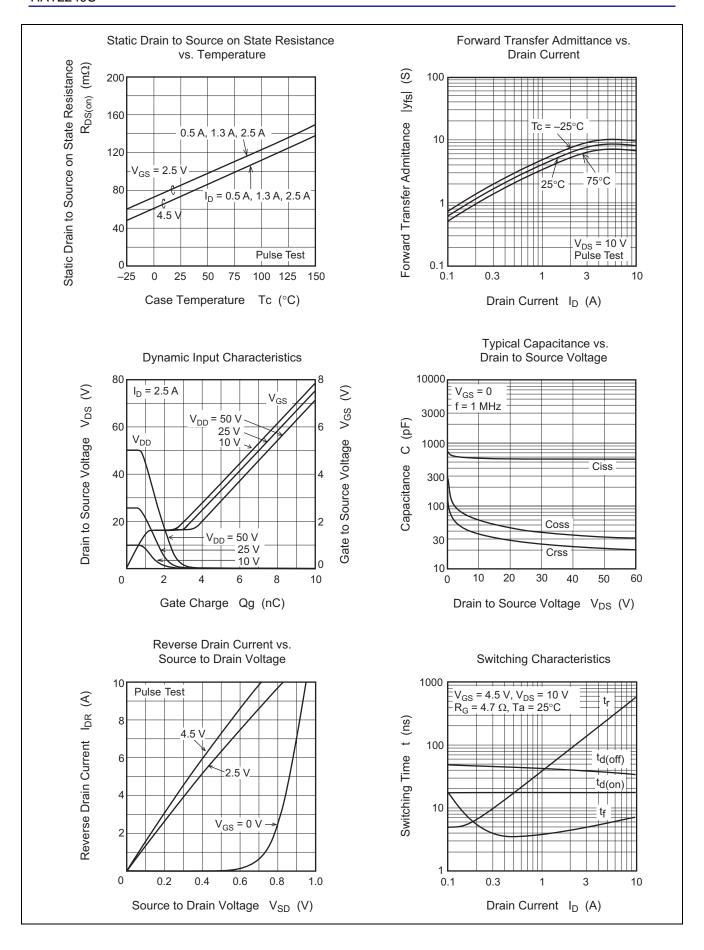
 $(Ta = 25^{\circ}C)$ 

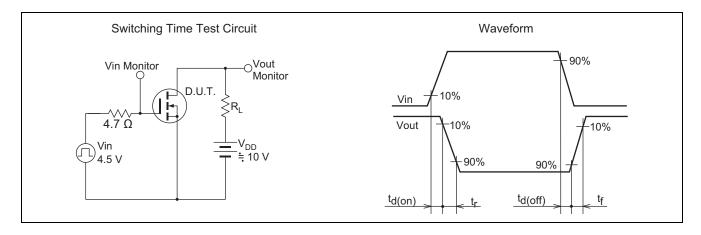
Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	60	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	±12				$I_G = \pm 100 \ \mu A, \ V_{DS} = 0$
Gate to source leak current	I <sub>GSS</sub>	_	_	±10	μΑ	$V_{GS} = \pm 10 \text{ V}, V_{DS} = 0$
Drain to source leak current	I <sub>DSS</sub>	_	_	1	μΑ	$V_{DS} = 60 \text{ V}, V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	0.4	_	1.4	V	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$
Drain to source on state resistance	R <sub>DS(on)</sub>	_	75	98	mΩ	$I_D = 1.3 \text{ A}, V_{GS} = 4.5 \text{ V}^{\text{Note3}}$
	R <sub>DS(on)</sub>	_	85	119	mΩ	$I_D = 1.3 \text{ A}, V_{GS} = 2.5 \text{ V}^{\text{Note3}}$
Forward transfer admittance	y <sub>fs</sub>	3.3	5	_	S	$I_D = 1.3 \text{ A}, V_{DS} = 10 \text{ V}^{\text{Note3}}$
Input capacitance	Ciss	_	590	_	pF	$V_{DS} = 10 \text{ V}, V_{GS} = 0,$
Output capacitance	Coss	_	60	_	pF	f = 1 MHz
Reverse transfer capacitance	Crss	_	35	_	pF	
Total gate charge	Qg	_	6	_	nC	V <sub>DD</sub> = 10 V, V <sub>GS</sub> = 4.5 V
Gate to source charge	Qgs	_	1.2	_	nC	$I_D = 2.5 \text{ A}$
Gate to drain charge	Qgd	_	1.4	_	nC	
Turn - on delay time	t <sub>d(on)</sub>	_	17	_	ns	I <sub>D</sub> = 1.3 A
Rise time	t <sub>r</sub>	_	50	_	ns	$V_{GS} = 4.5 \text{ V}, V_{DD} = 10 \text{ V}$
Turn - off delay time	t <sub>d(off)</sub>	_	41	_	ns	$R_L = 7.7 \Omega$ , $Rg = 4.7 \Omega$
Fall time	t <sub>f</sub>	_	4	_	ns	
Body - drain diode forward voltage	$V_{DF}$	_	0.8	1.1	V	$I_F = 2.5 \text{ A}, V_{GS} = 0^{\text{Note3}}$

Notes: 3. Pulse test

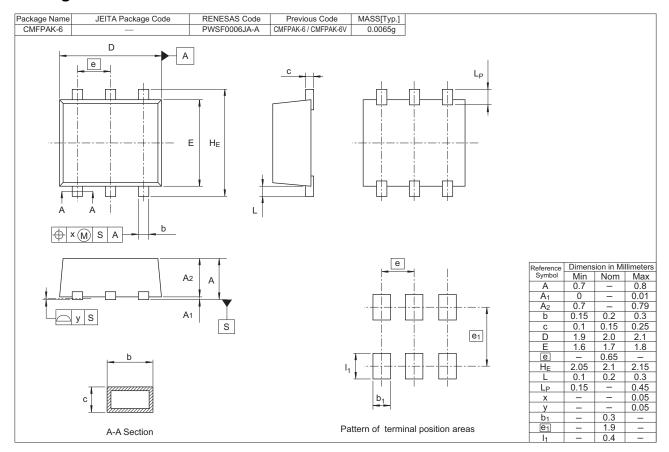
### **Main Characteristics**







# **Package Dimensions**



# **Ordering Information**

Orderable Part Number	Quantity	Shipping Container
HAT2240C-EL-E	3000 pcs	Taping

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